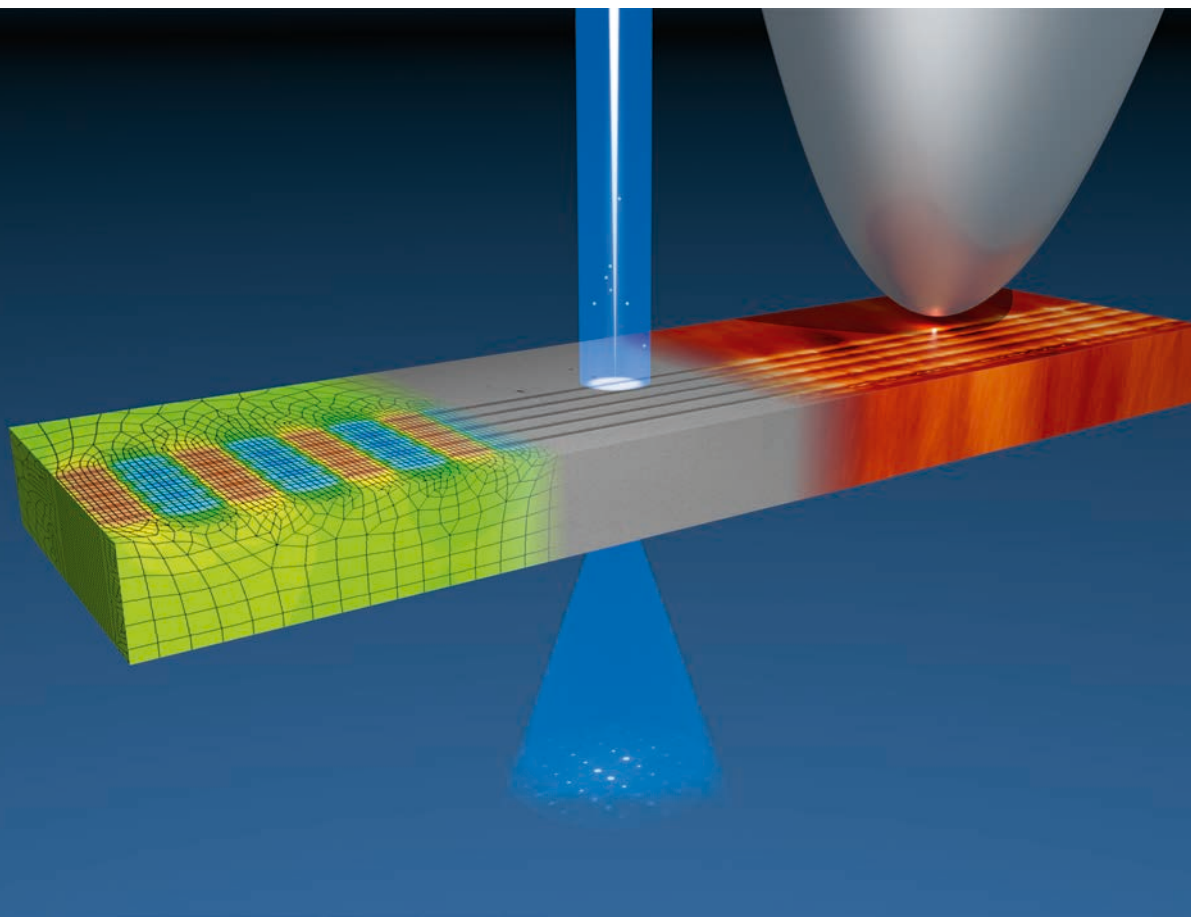


Investigation of ternary nitride semiconductor alloys by scanning tunneling microscopy

Verena Portz



Information
Band/ Volume 48
ISBN 978-3-95806-232-0

Forschungszentrum Jülich GmbH
Peter Grünberg Institute (PGI)
Microstructure Research (PGI-5)

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Schriften des Forschungszentrums Jülich
Reihe Information / Information

Band / Volume 48

ISSN 1866-1777

ISBN 978-3-95806-232-0

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